

### Features

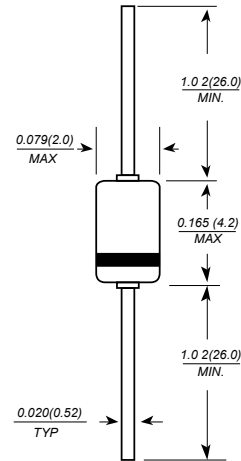
- For general purpose applications
- These diodes feature very low turn-on voltage and fast switching. These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharges.

### Mechanical Data

- Case: DO-35, glass case
- Polarity: Color band denotes cathode
- Weight: 0.004 ounces, 0.13 grams



### DO-35(GLASS)



Dimensions in millimeters

### Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	20	V
Continuous Forward Current	$I_F$	350	mA
Repetitive Peak Forward Current at $t_p < 10$ ms,	$I_{FRM}$	1	A
Forward Surge Current at $t_p < 10$ ms,	$I_{FSM}$	7.5	A
Power Dissipation , $T_a = 65$ °C	$P_D$	330	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	300	°C/W
Junction Temperature	$T_J$	125	°C
Ambient Operating Temperature Range	$T_a$	-65 to + 125	°C
Storage temperature range	$T_S$	-65 to + 150	°C

Note: (1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature.

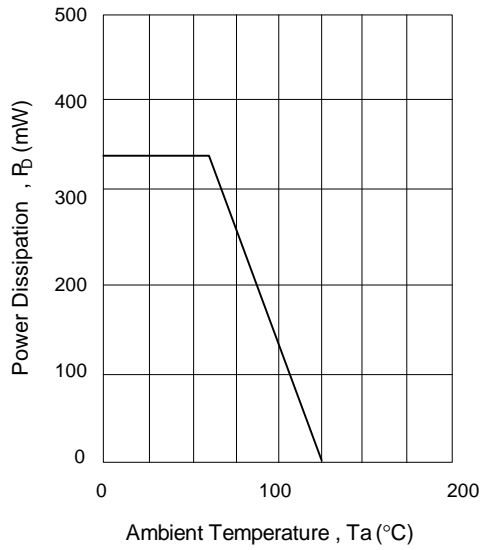
### Electrical Characteristics ( $T_J = 25$ °C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 100 \mu A$ (pulsed)	40	-	-	V
Reverse Current	$I_R$	$V_R = 10$ V	-	-	2	$\mu A$
Pulse Test $t_p < 300 \mu s$ , $\delta < 2\%$		$V_R = 20$ V	-	-	5	
		$V_R = 40$ V	-	-	25	
Forward Voltage	$V_F$	$I_F = 1$ mA	-	-	0.30	V
Pulse Test $t_p < 300 \mu s$ , $\delta < 2\%$		$I_F = 10$ mA	-	-	0.40	
		$I_F = 30$ mA	-	-	0.50	
		$I_F = 100$ mA	-	-	0.75	
		$I_F = 500$ mA	-	-	0.90	
Diode Capacitance	$C_d$	$V_R = 1$ V, $f = 1$ MHz	-	12	-	pF

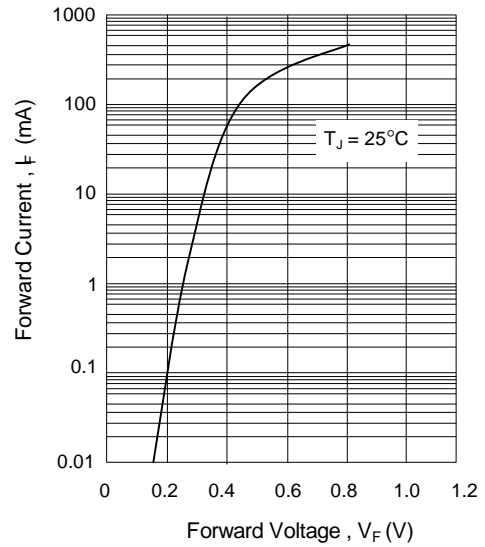


## RATING AND CHARACTERISTIC CURVES (BAT47)

**Admissible Power Dissipation vs. Ambient Temperature**



**Typical Forward Characteristics**



**Typical Reverse Characteristics**

